

HEWLETT
PACKARD

查询ASP0955供应商

ASP-0955
 推荐邦 专业PCB打样工厂, 24小时
 55 Watt, 900 MHz
 Silicon Power Transistor 加急出货

Features

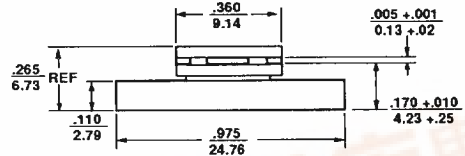
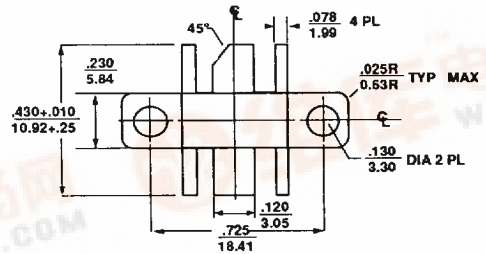
- Power Out: 55 Watts
- Common Base Class C Power Transistor
- Frequency: 800-960 MHz
- Voltage: 25 V
- Efficiency: 50% Min.
- Load Mismatch Tolerance: 4.3:1

Description

The ASP-0955 is a large signal, Class C common base, NPN silicon bipolar power transistor, housed in a BeO flange package for excellent thermal transfer. This device is designed for use as a 55 W driver or output amplifier for base station applications in cellular telephone systems operating in the 830 to 960 MHz frequency range.

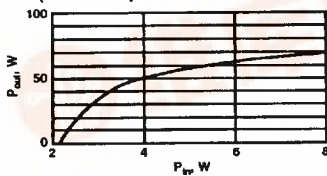
Excellent device uniformity, performance and reliability are produced by the use of ion-implantation, self-alignment techniques, and gold metallization in the fabrication of these devices. Emitter ballasting ensures a rugged device capable of withstanding severe load mismatches.

Power Flange

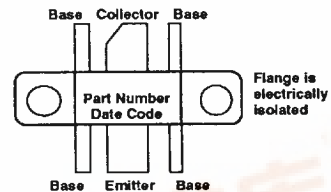


Dimensions are $\frac{\text{in}}{\text{mm}}$
 Tolerances: in .xxx = ± 0.005 mm .xx = ± 0.13

Power Output vs. Power Input
 $V_{CE} = 25 \text{ V}$, $f = 900 \text{ MHz}$
 (Broadband performance in demo circuit)



Marking and Lead Configuration



Electrical Specifications, $T_A = 25^\circ\text{C}$

Symbol	Parameters and Test Conditions	Units	Min.	Typ.	Max.
P_{out}	Output Power ¹ $V_{CE} = 25 \text{ V}$, $P_{in} = 7 \text{ W}$, $f = 900 \text{ MHz}$	Watts	55	58	
G_P	Power Gain ¹ $V_{CE} = 25 \text{ V}$, $P_{in} = 7 \text{ W}$, $f = 900 \text{ MHz}$	dB	8.9	9.2	
η_C	Collector Efficiency ¹ $V_{CE} = 25 \text{ V}$, $P_{in} = 7 \text{ W}$, $f = 900 \text{ MHz}$	%	50	55	
	Load Mismatch Tolerance $V_{CE} = 25 \text{ V}$, rated P_{out} , $f = 900 \text{ MHz}$	-	4.3:1		
BV_{CED}	Collector-Emitter Voltage $V_{EB} = \text{open}$, $I_C = 50 \text{ mA}$	V	24	28	
BV_{CES}	Collector-Emitter Voltage $V_{EB} = 0 \text{ V}$, $I_C = 100 \text{ mA}$	V	50	55	
BV_{EBO}	Emitter-Base Voltage $V_{CB} = \text{open}$, $I_E = 15 \text{ mA}$	V	3.5	4.5	
h_{FE}	Forward Current Transfer Ratio $V_{CE} = 5 \text{ V}$, $I_C = 3 \text{ A}$	-	20	60	120
I_{CES}	Collector Leakage Current $V_{CE} = 26 \text{ V}$	mA		1	15
C_{OB}	Collector-Base Capacitance $f = 1 \text{ MHz}$, $V_{CB} = 25 \text{ V}$, $I_E = 0 \text{ mA}$	pF		62	

Notes: 1 Tuned narrow band test.



ASP-0955
55 Watt, 900 MHz Class C Power Transistor

Absolute Maximum Ratings

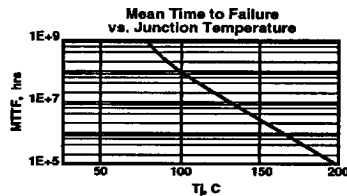
Parameter	Symbol	Absolute Maximum ¹
Emitter-Base Voltage	V_{EBO}	4.0 V
Collector-Emitter Voltage	V_{CES}	50 V
Collector Current	I_C	8.0 A
Power Dissipation ^{2,3}	P_T	115 W
Junction Temperature	T_j	200°C
Storage Temperature	T_{STG}	-65 to 150°C

Thermal Resistance²: $\theta_{jC} = 1.2^\circ\text{C/W}$

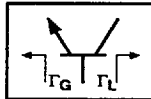
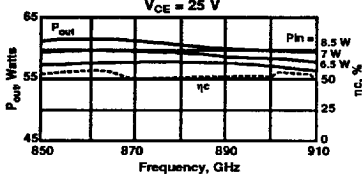
Notes:

1. Operation of this device above any one of these parameters may cause permanent damage.
2. $T_{case} = 25^\circ\text{C}$
3. Derate at .83 W/°C for $T_{case} > 62^\circ\text{C}$

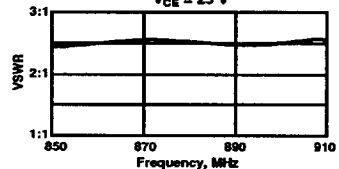
Typical Performance, $T_A = 25^\circ\text{C}$
 (Unless otherwise noted.)



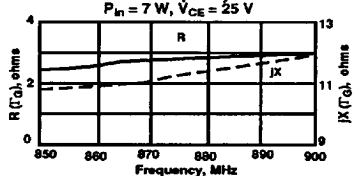
Typical Broadband Performance
 Output Power and Collector Efficiency vs. Frequency and Input Power
 $V_{CE} = 25\text{ V}$



Typical Broadband Performance
 Input VSWR vs. Frequency
 $V_{CE} = 25\text{ V}$

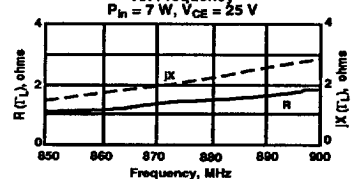


Typical Generator Impedance vs. Frequency
 $P_{in} = 7\text{ W}, V_{CE} = 25\text{ V}$

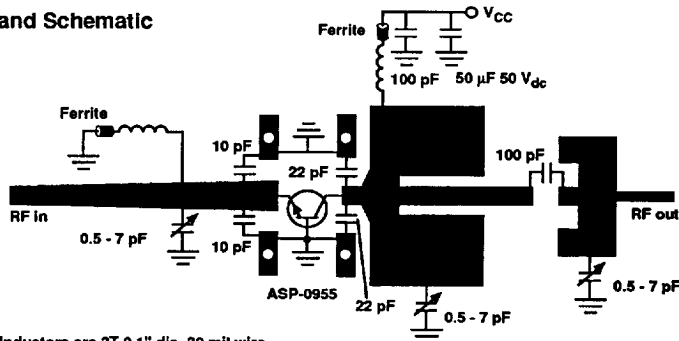


Freq. MHz	Γ_G		Γ_L	
	R	jX	R	jX
850	2.5	10.8	1.3	1.6
860	2.6	11.0	1.4	1.8
870	2.8	11.2	1.5	2.0
880	2.9	11.5	1.6	2.3
890	3.0	11.7	1.8	2.6
900	3.1	12.0	2.0	2.9

Typical Load Impedance vs. Frequency
 $P_{in} = 7\text{ W}, V_{CE} = 25\text{ V}$



Test Circuit Layout and Schematic
850-900 MHz



(not to scale)

Inductors are 3T 0.1" dia. 30 mil wire